TV-03
www.oxfordplasma.de/process/dse_mesa.htm

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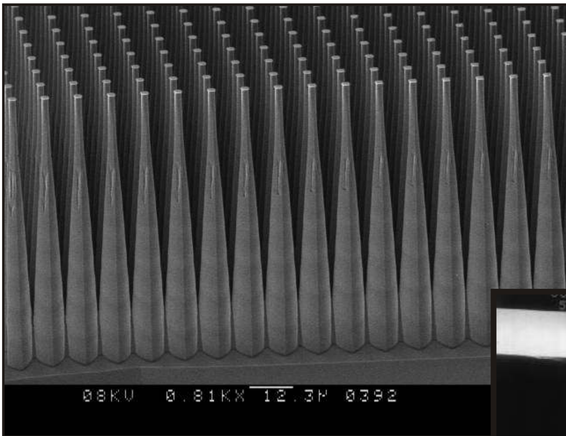
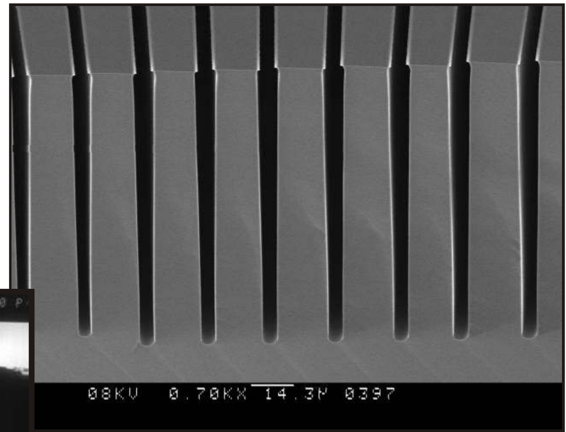
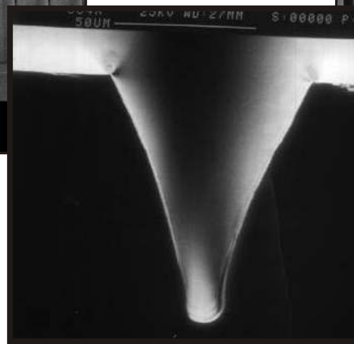
Plasmalab Data

Anisotropic SF_6 / O_2 Deep Si Etching (ICP) by temperature control: high rates and very high selectivities without sidewall polymers



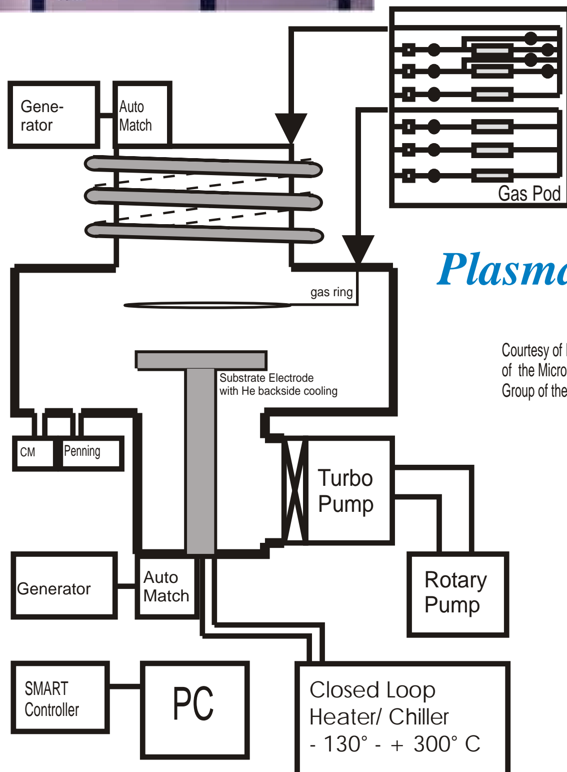




25 - 30 µm deep etches in Si
aspect ratio 10 : 1 up to 25 : 1
ca 1 µm / min for high aspect ratios

500 µm deep via holes through the wafer
up to 20 µm / min for larger features

selectivity to the PR and SiO2 masks
150 - 200 : 1 up to > 1.000 : 1 !



Plasmalab System 100

Courtesy of Prof. Dr. M.C. Elwenspoek
of the Micromechanical Transducers
Group of the MESA Research Institute